

1. General description

Planar passivated sensitive gate four quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in general purpose bidirectional switching and phase control applications. This sensitive gate "series E" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

2. Features and benefits

- Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- · Planar passivated for voltage ruggedness and reliability
- Sensitive gate
- Triggering in all four quadrants

3. Applications

- General purpose motor control
- General purpose switching

4. Quick reference data

k reference data					
Parameter	Conditions	Min	Тур	Max	Unit
repetitive peak off- state voltage		-	-	600	V
non-repetitive peak on- state current	full sine wave; T _{j(init)} = 25 °C; t _p = 20 ms; <u>Fig. 4; Fig. 5</u>	-	-	95	A
junction temperature		-	-	125	°C
RMS on-state current	full sine wave; T _{mb} ≤ 99 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	-	12	A
eristics					-,
gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	-	2.5	10	mA
	V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 7</u>	-	4	10	mA
	Parameter repetitive peak off- state voltage non-repetitive peak on- state current junction temperature RMS on-state current eristics	ParameterConditionsrepetitive peak off- state voltagenon-repetitive peak on- state currentfull sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 20 ^{\circ}ms; Fig. 4; Fig. 5$ junction temperatureRMS on-state currentfull sine wave; $T_{mb} \leq 99 ^{\circ}C$; Fig. 1; Fig. 2; Fig. 3pristicsgate trigger current $V_D = 12 ^{\circ}V; I_T = 0.1 ^{\circ}A; T2+ G+;$ $T_j = 25 ^{\circ}C; Fig. 7$ $V_D = 12 ^{\circ}V; I_T = 0.1 ^{\circ}A; T2+ G-;$	ParameterConditionsMinrepetitive peak off- state voltage-non-repetitive peak on- state currentfull sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 20 ms; Fig. 4; Fig. 5$ -junction temperature-RMS on-state currentfull sine wave; $T_{mb} \le 99 ^{\circ}C$; Fig. 1; Fig. 2; Fig. 3-pristicsgate trigger current $V_D = 12 V; l_T = 0.1 A; T2+ G+;$ $T_j = 25 ^{\circ}C; Fig. 7$ - $V_D = 12 V; l_T = 0.1 A; T2+ G-;$ -	ParameterConditionsMinTyprepetitive peak off- state voltagenon-repetitive peak on- state currentfull sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 20 ms; Fig. 4; Fig. 5$ junction temperatureImage: full sine wave; $T_{mb} \le 99 ^{\circ}C$; Fig. 1; Fig. 2; Fig. 3RMS on-state currentfull sine wave; $T_{mb} \le 99 ^{\circ}C$; Fig. 1; Fig. 2; Fig. 3pristicsgate trigger current $V_D = 12 ^{\circ}V; I_T = 0.1 ^{\circ}A; T2+ G+;$ $T_j = 25 ^{\circ}C; Fig. 7$ -4	ParameterConditionsMinTypMaxrepetitive peak off- state voltage600non-repetitive peak on- state currentfull sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 20 ms; Fig. 4; Fig. 5$ 95junction temperature125RMS on-state currentfull sine wave; $T_{mb} \le 99 ^{\circ}C$; Fig. 1; Fig. 2; Fig. 312pristicsgate trigger current $V_D = 12 ^{\circ}V; I_T = 0.1 ^{\circ}X; T2 + G^+;$ $T_j = 25 ^{\circ}C; Fig. 7$ -410





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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{7}$	-	5	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; <u>Fig. 7</u>	-	11	25	mA
Dynamic char	acteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	-	150	-	V/µs

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2
2	T2	main terminal 2		sym051
3	G	gate		
mb	T2	mounting base; main terminal 2		
			TO-220AB (SOT78)	

6. Ordering information

Table 3. Ordering	g information					
Type number	Package					
	Name	Description	Version			
BT138-600E	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			
BT138-600E/DG	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

7. Marking

Table 4. Marking codes	
Type number	Marking code
BT138-600E	
BT138-600E/DG	BT138-600EDG

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8. Limiting values

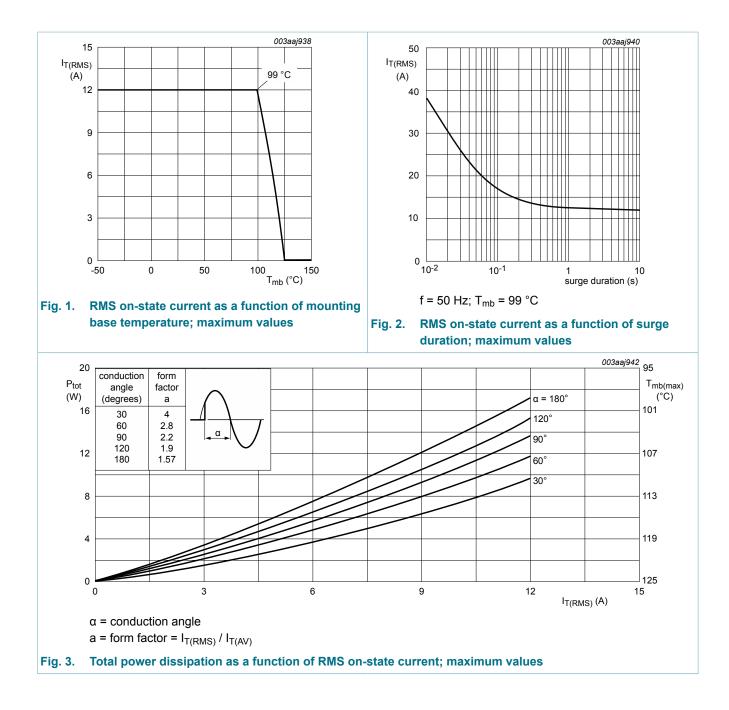
Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 99$ °C; Fig. 1; Fig. 2; Fig. 3	-	12	A
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 20 \text{ ms}; Fig. 4; Fig. 5$	-	95	A
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms	-	105	A
l ² t	I ² t for fusing	t_p = 10 ms; sine-wave pulse	-	45	A ² s
dl _T /dt	rate of rise of on-state current	I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/µs; T2+ G+	-	50	A/µs
		I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/µs; T2+ G-	-	50	A/µs
		I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/µs; T2- G-	-	50	A/µs
		I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/µs; T2- G+	-	10	A/µs
I _{GM}	peak gate current		-	2	А
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

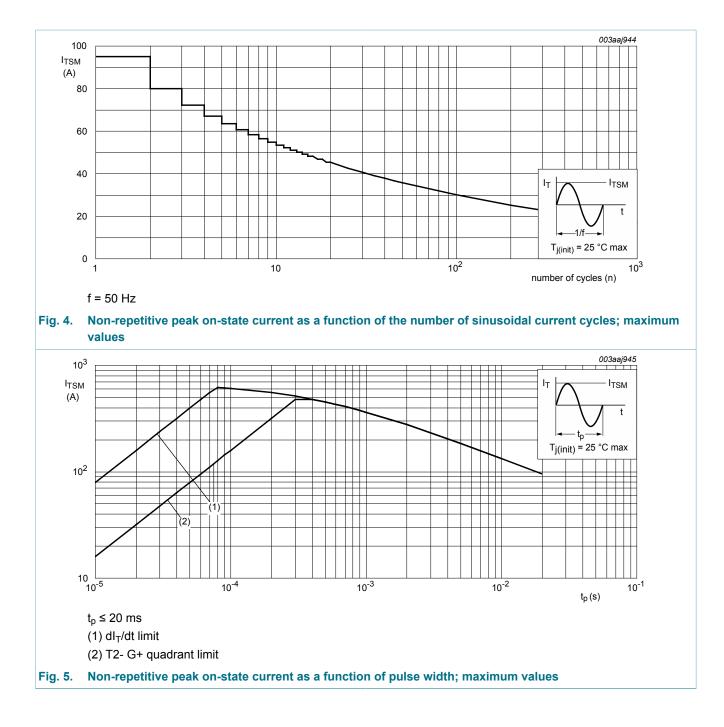
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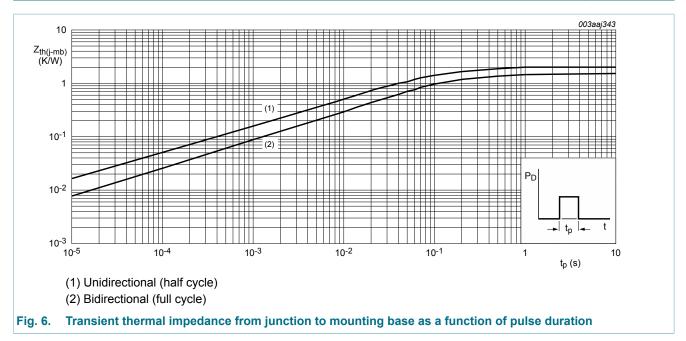
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9. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance	full cycle; <u>Fig. 6</u>	-	-	1.5	K/W
	from junction to mounting base	half cycle; <u>Fig. 6</u>	-	-	2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W



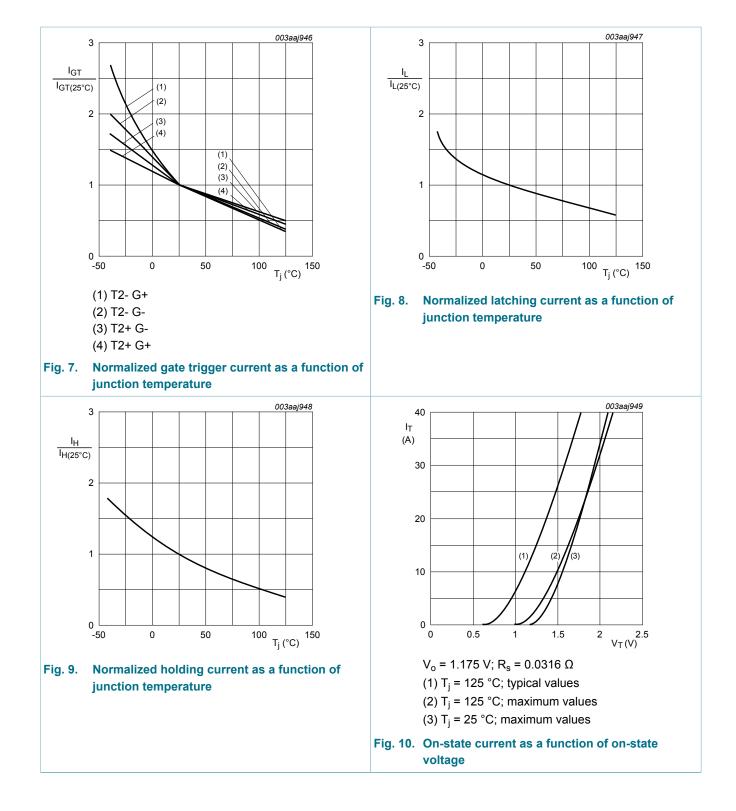
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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics			_		_
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	-	2.5	10	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 7</u>	-	4	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 7</u>	-	5	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; <u>Fig. 7</u>	-	11	25	mA
lL	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 8</u>	-	-	30	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 8</u>	-	-	40	mA
		V _D = 12 V; I _G = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 8</u>	-	-	30	mA
		V _D = 12 V; I _G = 0.1 A; T2- G+; T _j = 25 °C; <u>Fig. 8</u>	-	-	40	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	30	mA
V _T	on-state voltage	I _T = 15 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.4	1.65	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 11	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic cł	naracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	-	150	-	V/µs
t _{gt}	gate-controlled turn-on time	I_{TM} = 16 A; V_D = 600 V; I_G = 0.1 A; dI_G/dt = 5 A/µs	-	2	-	μs
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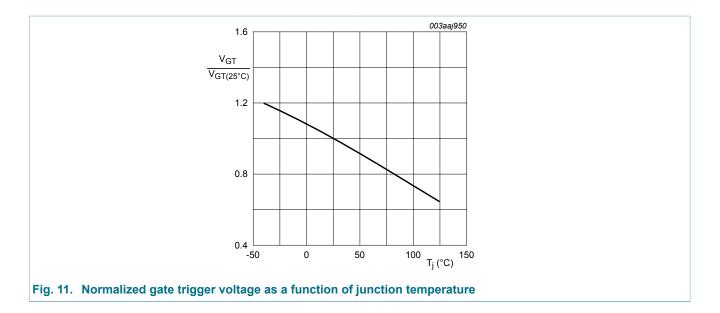


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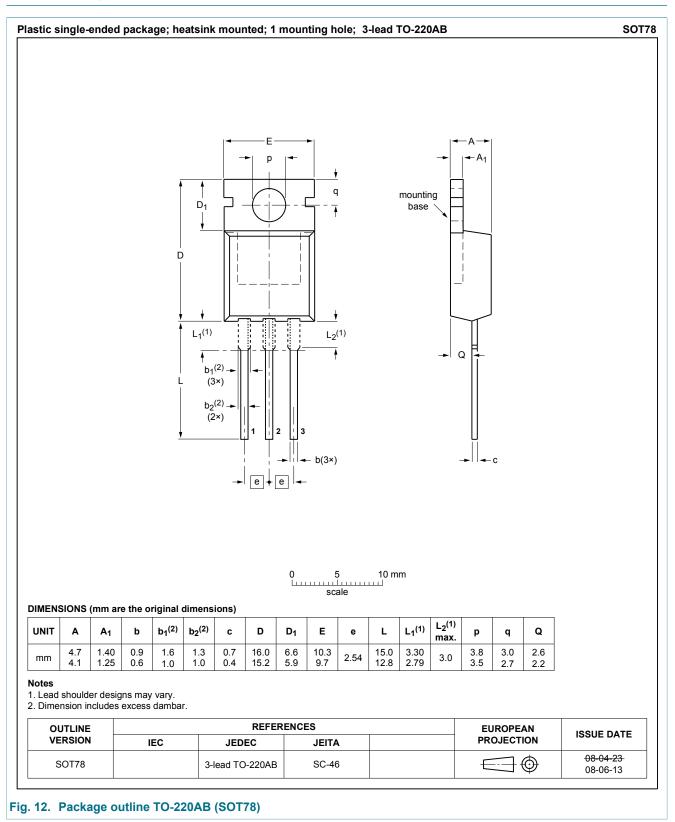
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11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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